

• General Description

The ZMS095N12N combines advanced Trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

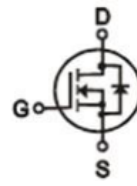
- Synchronous Rectification for AC-DC/DC-DC converter
- Oring switches
- Power Tools

• Ordering Information:

Part NO.	ZMS095N12N
Marking	ZMS095N12
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

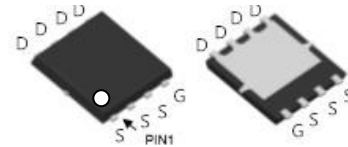
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current($T_C=25^\circ\text{C}$)	$I_{D@TC=25^\circ\text{C}}$	60	A
	$I_{D@TC=75^\circ\text{C}}$	45	A
	$I_{D@TC=100^\circ\text{C}}$	38	A
Pulsed Drain Current ①	I_{DM}	180	A
Total Power Dissipation($T_C=25^\circ\text{C}$)	$P_D@TC=25^\circ\text{C}$	85	W
Total Power Dissipation($T_A=25^\circ\text{C}$)	$P_D@TA=25^\circ\text{C}$	3.4	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	50	mJ
Avalanche Current@L=0.1mH	I_{AS}	35	A

• Product Summary


$V_{DS} = 120\text{V}$

$R_{DS(ON)} = 9.5\text{m}\Omega$

$I_D = 60\text{A}$


DFN5 x 6

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	1.5	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	37	° C/W
Soldering temperature, wave soldering for 10s	T _{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	120			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.2		2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =120V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =25A		9.5	12	mΩ
		V _{GS} =4.5V, I _D =15A		12	16	mΩ
Forward Transconductance	g _{FS}	V _{DS} =25V, I _D =10A		24		s
Source-drain voltage	V _{SD}	I _S =25A		0.85	1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =20V f = 1MHz	-	2380	-	pF
Output capacitance	C _{oss}		-	928	-	
Reverse transfer capacitance	C _{rss}		-	48	-	

•Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 25V	-	30	-	nC
Gate - Source charge	Q _{gs}	I _D = 8A	-	4.4	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	6.6	-	
Body Diode Reverse Recovery Time	t _{rr}	I _F =20A, di/dt=100A/μs		47		nS
Body Diode Reverse Recovery Charge	Q _{rr}	I _F =20A, di/dt=100A/μs		38		nC

Note: ① Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$;

Fig.1 Gate-Charge Characteristics

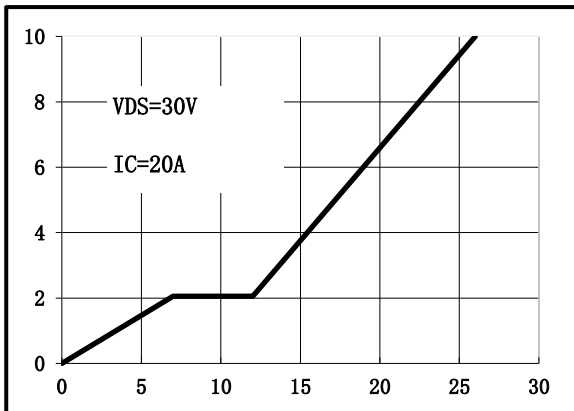


Fig.2 Capacitance Characteristics

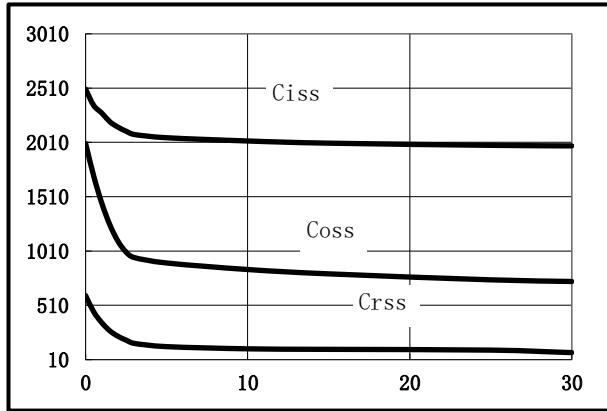


Fig.3 Power Dissipation

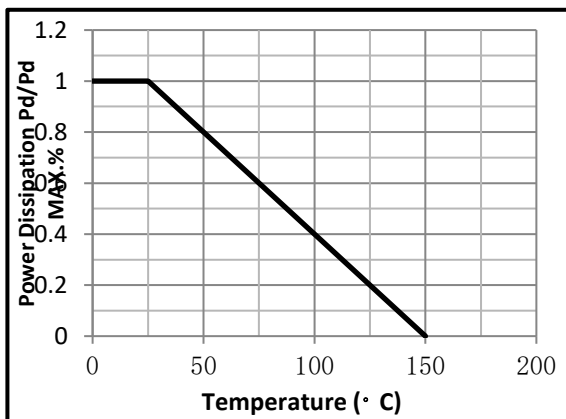


Fig.4 Typical output Characteristics

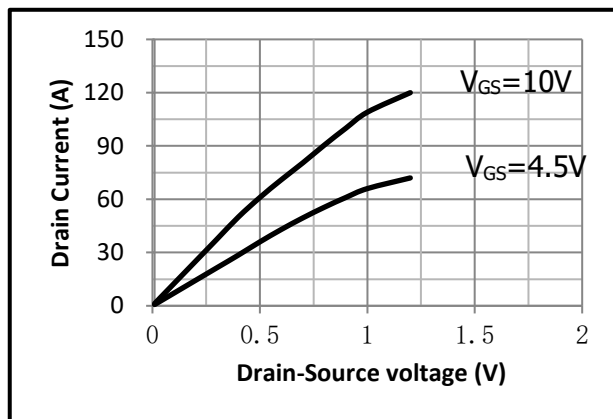


Fig.5 Threshold Voltage V.S Junction Temperature

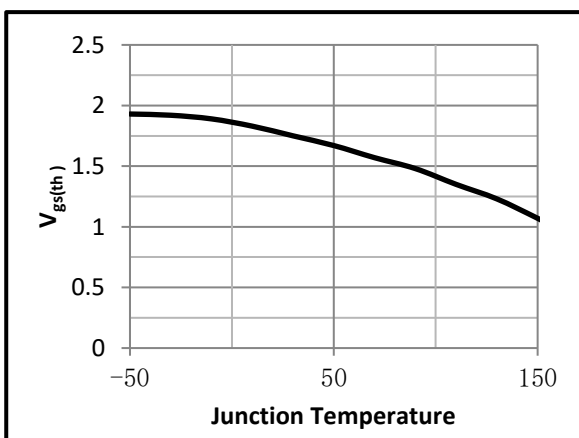


Fig.6 Resistance V.S Drain Current

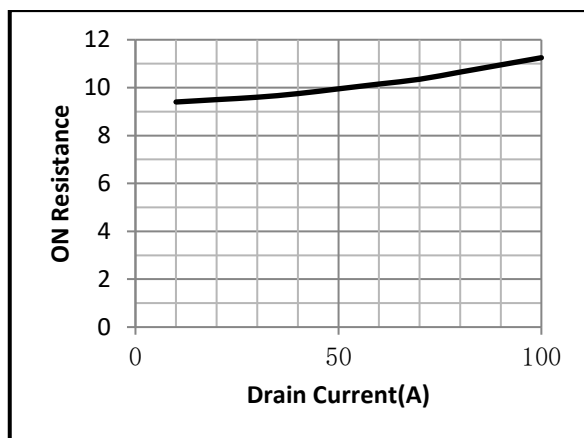


Fig.7 On-Resistance VS Gate Source Voltage

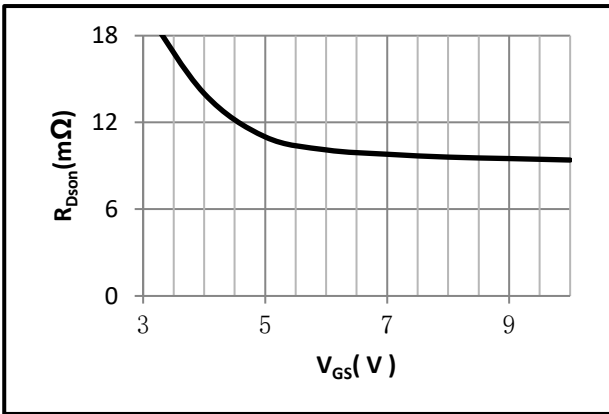


Fig.8 On-Resistance V.S Junction Temperature

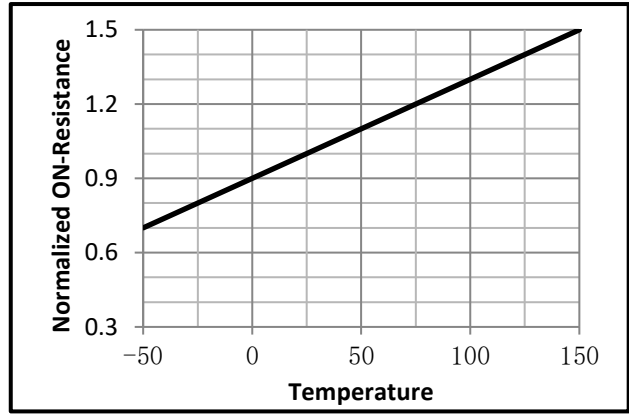


Fig.9 Switching Time Measurement Circuit

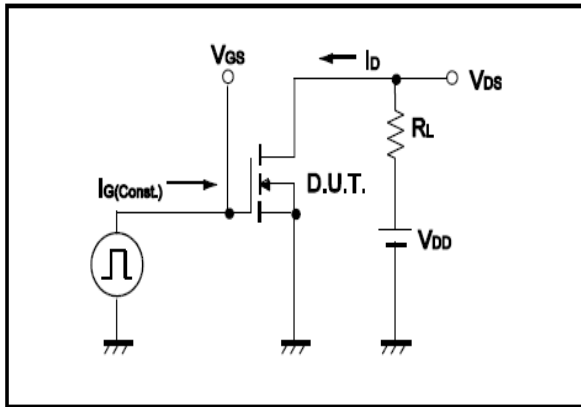


Fig.10 Gate Charge Waveform

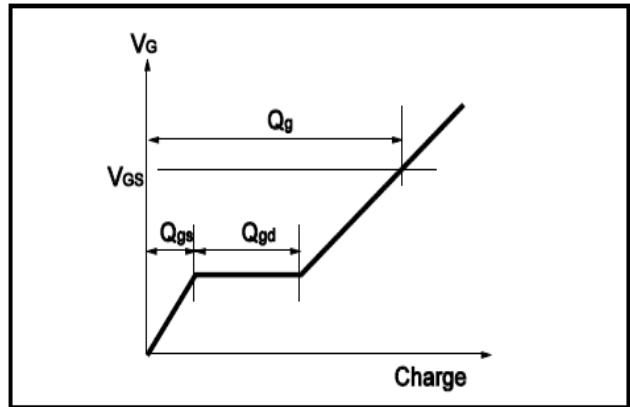


Fig.11 Switching Time Measurement Circuit

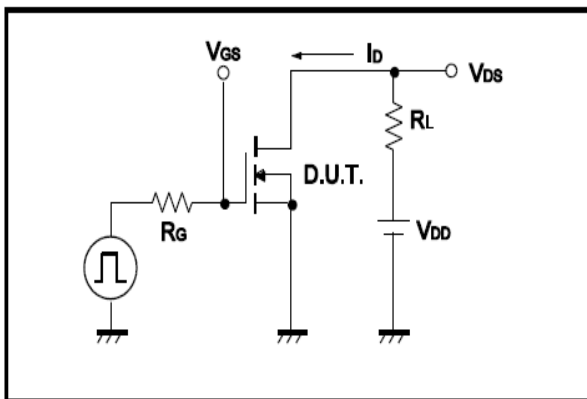


Fig.12 Gate Charge Waveform

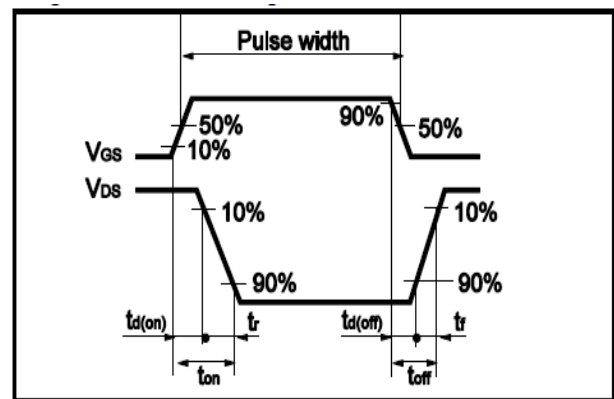


Fig.13 Avalanche Measurement Circuit

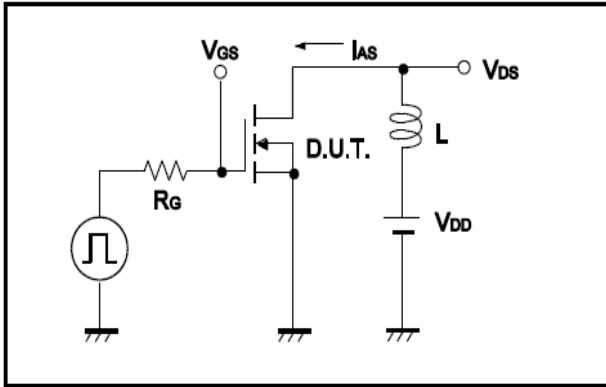
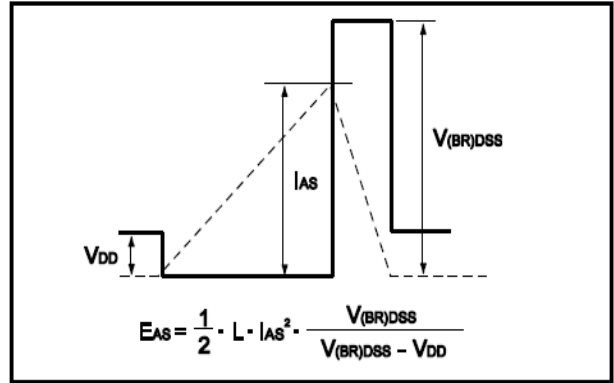


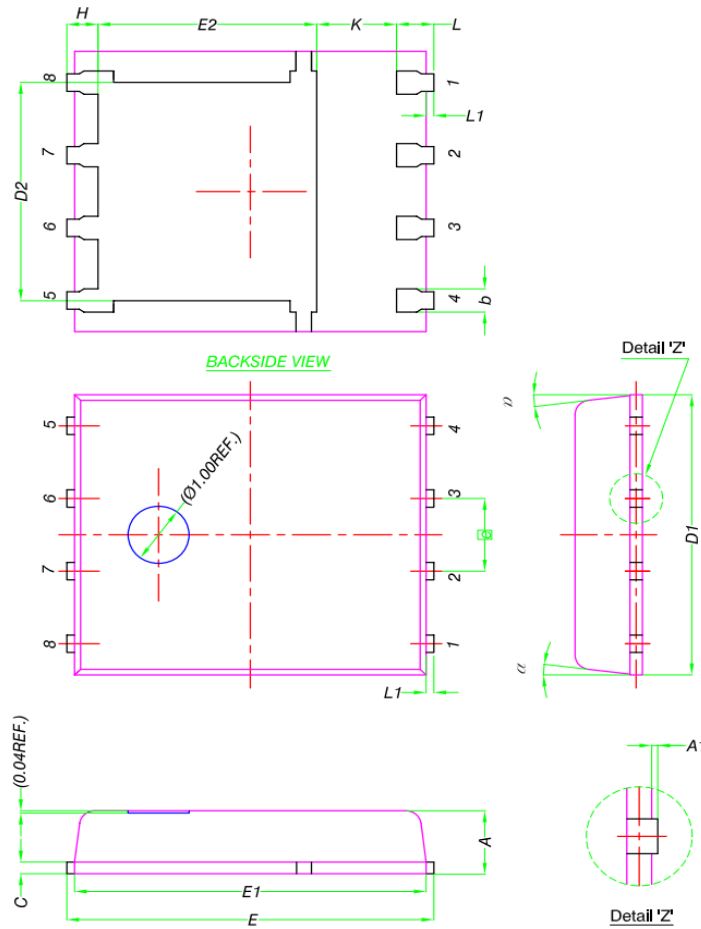
Fig.14 Avalanche Waveform





•Dimensions (DFN5x6)

Unit: mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
$\square e$	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°